

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1721

HIGH VOLTAGE CONTROL APPLICATIONS.

PLASMA DISPLAY, NIXIE TUBE DRIVER APPLICATIONS.

CATHODE RAY TUBE BRIGHTNESS CONTROL APPLICATIONS.

- High Voltage : $V_{CBO} = -300V$, $V_{CEO} = -300V$
- Low Saturation Voltage : $V_{CE}(\text{sat}) = -0.5V$ (Max.)
- Small Collector Output Capacitance : $C_{ob} = 5.5pF$ (Typ.)
- Complementary to 2SC4497

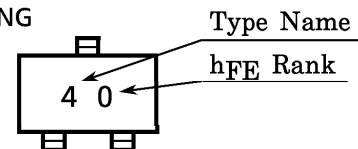
MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-100	mA
Base Current	I_B	-20	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

ELECTRICAL CHARACTERISTIC ($T_a = 25^\circ C$)

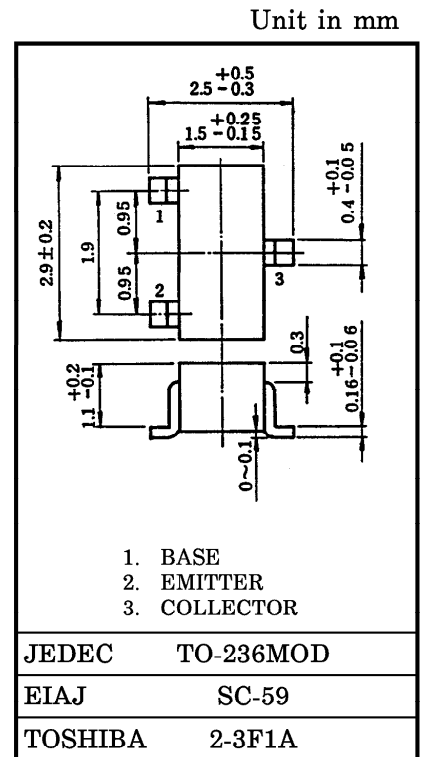
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -300V, I_E = 0$	—	—	-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-0.1	μA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-300	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-300	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -10V, I_C = -20mA$	30	—	150	
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -1mA$	20	—	—	
Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_C = -20mA, I_B = -2mA$	—	—	-0.5	V
Base-Base Saturation Voltage	$V_{BE}(\text{sat})$	$I_C = -20mA, I_B = -2mA$	—	—	-1.2	V
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -20mA$	50	55	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -20V, I_E = 0, f = 1MHz$	—	5.5	6.0	pF

Note : $h_{FE(1)}$ Classification R:30~90 0:50~150 MARKING

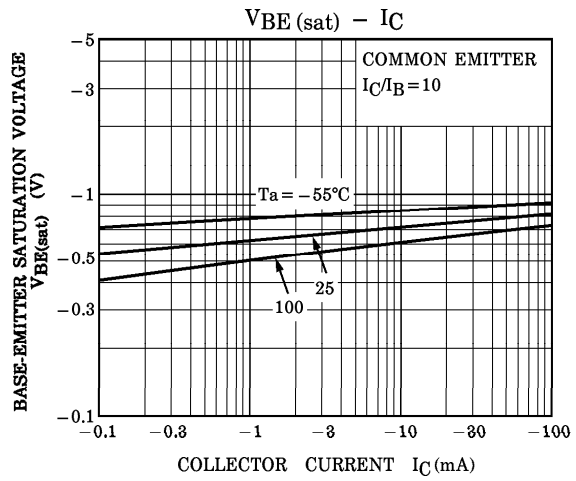
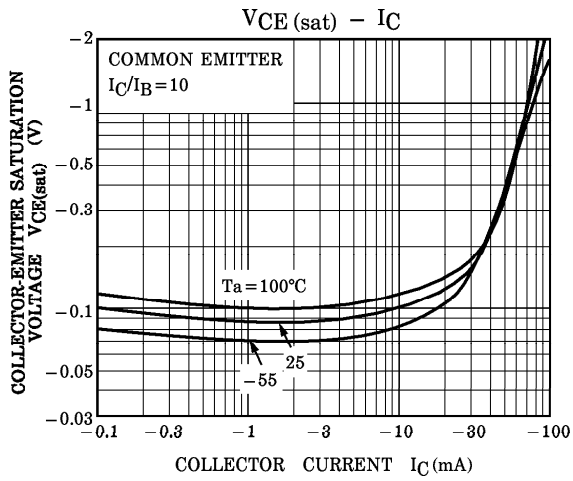
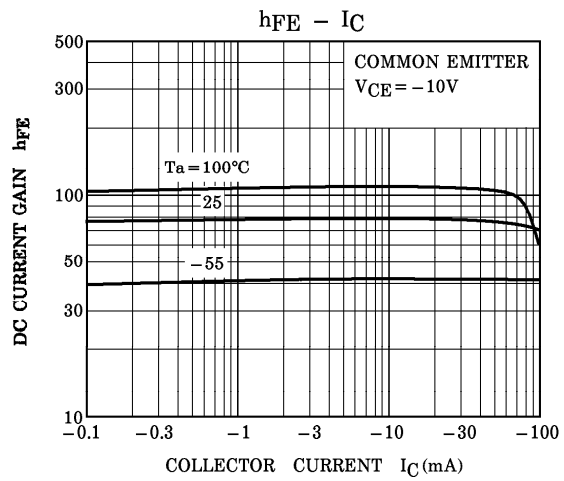
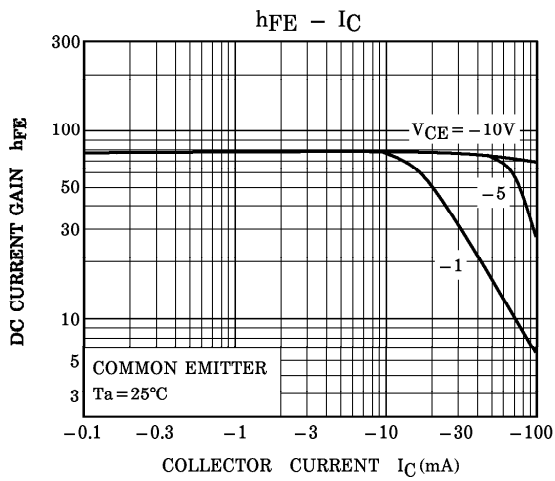
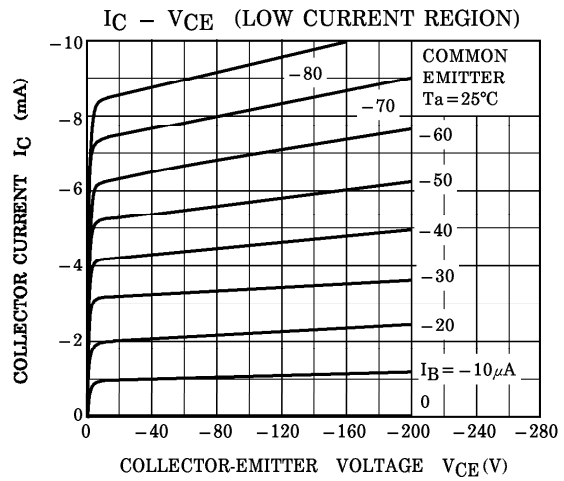
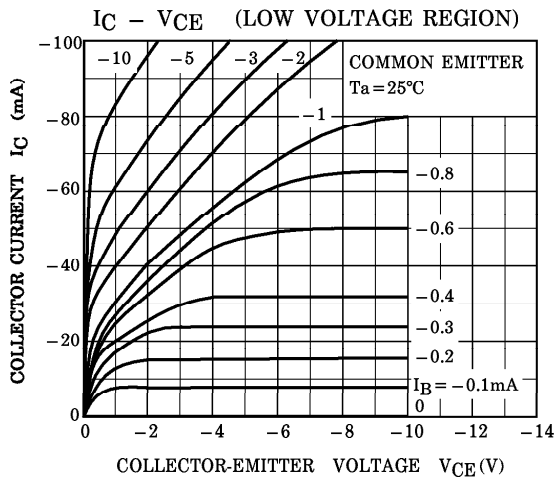


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Weight : 0.012g



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